

NP90N055VUK

MOS FIELD EFFECT TRANSISTOR

R07DS0578EJ0100 Rev.1.00 Nov 29, 2011

Description

The NP90N055VUK is N-channel MOS Field Effect Transistor designed for high current switching applications.

Features

• Super low on-state resistance

 $R_{DS(on)} = 3.85 \text{ m}\Omega \text{ MAX.} (V_{GS} = 10 \text{ V}, I_D = 45 \text{ A})$

- Low C_{iss} : $C_{iss} = 4000 \text{ pF TYP.} (V_{DS} = 25 \text{ V})$
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Pac	Package	
NP90N055VUK-E1-AY *1	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	TO-252 (MP-3ZP)
NP90N055VUK-E2-AY *1			Taping (E2 type)	

Note: *1 Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	55	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±90	А
Drain Current (pulse) *1	I _{D(pulse)}	±360	А
Total Power Dissipation (T _C = 25°C)	P _{T1}	147	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.2	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to 175	°C
Repetitive Avalanche Current *2	I _{AR}	33	А
Repetitive Avalanche Energy *2	E _{AR}	108	mJ

Notes: *1 $\,T_{C}$ = 25°C, $P_{W} \leq$ 10 $\mu s,\, Duty\,\, Cycle \leq$ 1%

Thermal Resistance

^{*2} R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

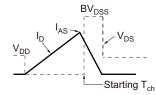
Electrical Characteristics (T_A = 25°C)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 55 \text{ V}, V_{GS} = 0 \text{ V}$	
Gate Leakage Current	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Forward Transfer Admittance *1	y _{fs}	30	60	_	S	$V_{DS} = 5 \text{ V}, I_{D} = 45 \text{ A}$	
Drain to Source On-state Resistance *1	R _{DS(on)}	_	3.20	3.85	mΩ	$V_{GS} = 10 \text{ V}, I_D = 45 \text{ A}$	
Input Capacitance	C _{iss}	_	4000	6000	pF	V _{DS} = 25 V	
Output Capacitance	Coss	_	410	620	pF	$V_{GS} = 0 V$	
Reverse Transfer Capacitance	C _{rss}	_	150	270	pF	f = 1 MHz	
Turn-on Delay Time	t _{d(on)}	_	25	60	ns	$V_{DD} = 28 \text{ V}, I_D = 45 \text{ A}$	
Rise Time	t _r	_	10	30	ns	$V_{GS} = 10 \text{ V}$	
Turn-off Delay Time	t _{d(off)}	_	65	130	ns	$R_G = 0 \Omega$	
Fall Time	t _f	_	6	20	ns		
Total Gate Charge	Q_G	_	68	102	nC	V _{DD} = 44 V	
Gate to Source Charge	Q_{GS}	_	18	_	nC	$V_{GS} = 10 \text{ V}$	
Gate to Drain Charge	Q_{GD}	_	18	_	nC	$I_D = 90 \text{ A}$	
Body Diode Forward Voltage *1	$V_{F(S-D)}$	_	0.9	1.5	V	I _F = 90 A, V _{GS} = 0 V	
Reverse Recovery Time	t _{rr}	_	47	_	ns	I _F = 90 A, V _{GS} = 0 V	
Reverse Recovery Charge	Q _{rr}	_	80	_	nC	di/dt = 100 A/μs	

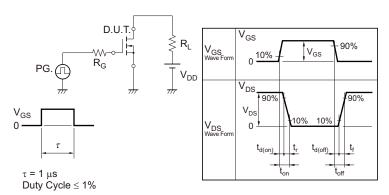
Note: *1 Pulsed test

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $V_{GS} = V_{DS}$ V_{DS}



TEST CIRCUIT 2 SWITCHING TIME

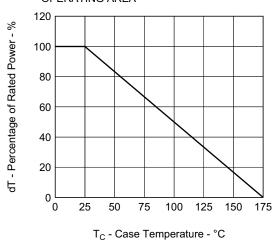


TEST CIRCUIT 3 GATE CHARGE

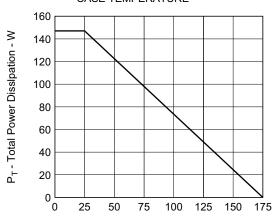
$$\begin{array}{c|c} D.U.T. \\ \hline I_G = 2 \text{ mA} \\ \hline \end{array} \\ \begin{array}{c} PG. \\ \hline \end{array} \\ \begin{array}{c} > 50 \Omega \\ \hline \end{array} \\ \end{array} \\ \begin{array}{c} V_{DD} \\ \hline \end{array}$$

Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

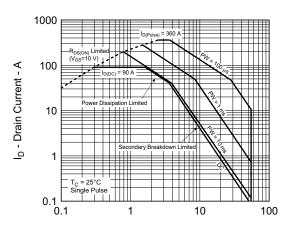


TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



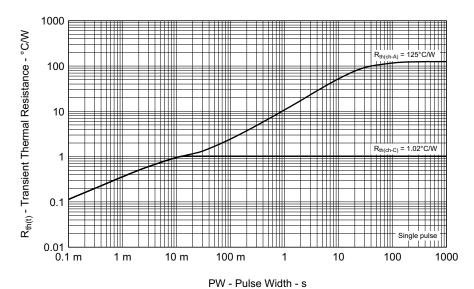
T_C - Case Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



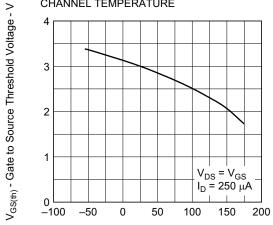
 V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



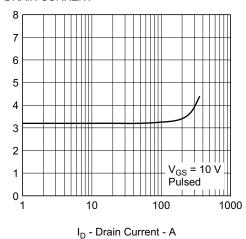
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE 400 350 I_D - Drain Current - A 300 250 200 150 100 $V_{GS} = 10 V$ 50 Pulsed 0.6 0.8 1.0 1.2 1.4 1.6 1.8 0 V_{DS} - Drain to Source Voltage - V



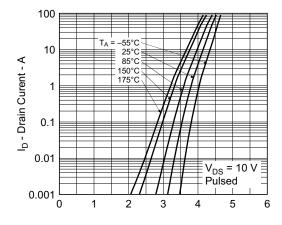


 T_{ch} - Channel Temperature - $^{\circ}\text{C}$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

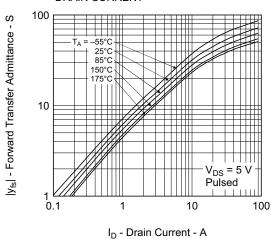


FORWARD TRANSFER CHARACTERISTICS

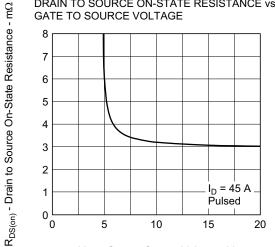


V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs.

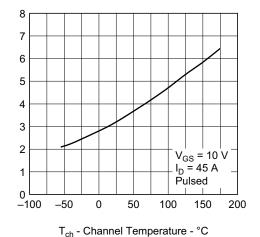


V_{GS} - Gate to Source Voltage - V

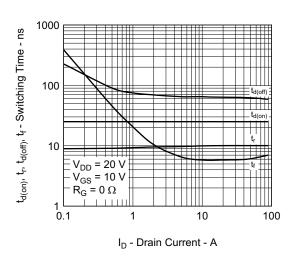
 $R_{DS(on)}$ - Drain to Source On-State Resistance - $m\Omega$

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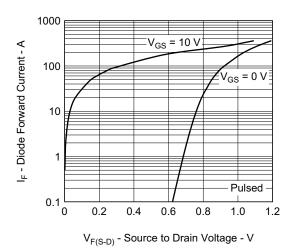
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



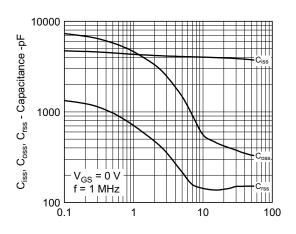
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

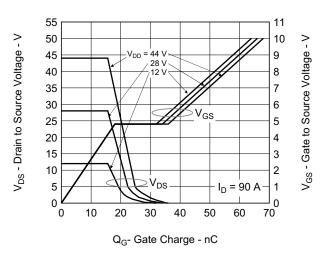


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

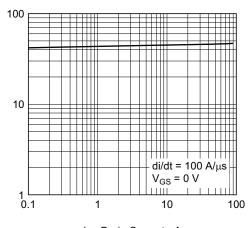


 V_{DS} - Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



REVERSE RECOVERY TIME vs. DRAIN CURRENT

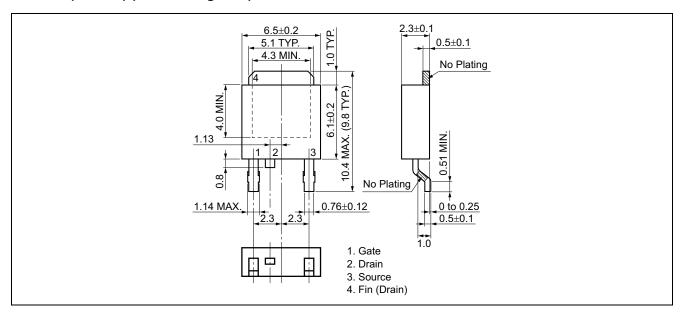


I_F - Drain Current - A

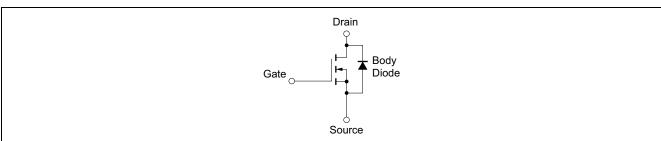
t_{rr} - Reverse Recovery Time - ns

Package Drawing (Unit: mm)

TO-252 (MP-3ZP) (Mass: 0.27 g TYP.)



Equivalent Circuit



Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History

NP90N055VUK Data Sheet

		Description		
Rev.	Date	Page	age Summary	
1.00	Nov 29, 2011	_	First Edition Issued	

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